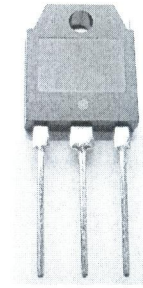


# BUX98AQ

Silicon NPN Transistors

B C E

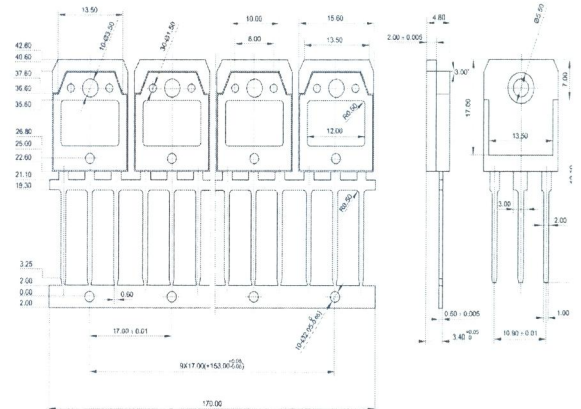


### ◆ Features

- With TO-3PN package
- This transistor is intended and industrial applications from single and three-phase mains operation.

### ◆ Absolute Maximum Ratings Tc=25□

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB</sub>	Collector to base voltage	1000	V
V <sub>CEO</sub>	Collector to emitter voltage	450	V
V <sub>EB</sub>	Emitter to base voltage	7.0	V
I <sub>CP</sub>	Peak Collector Current		
I <sub>C</sub>	Collector current-Continuous	30	A
P <sub>D</sub>	Total Power Dissipation@TC=25□	250	W
T <sub>j</sub>	Junction temperature	200	□
T <sub>stg</sub>	Storage temperature	-55~200	□



TO-3PN

### ◆ Electrical Characteristics Tc=25□

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I <sub>CBO</sub>	Collector-emitter breakdown voltage	V <sub>CB</sub> =1000V; I <sub>E</sub> =0		0.1	mA
I <sub>EBO</sub>	Emitter-base cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0		0.1	mA
I <sub>CEO</sub>	Collector-emitter Cutoff Current	V <sub>CE</sub> =450V; I <sub>B</sub> =0		2	mA
V <sub>CB0</sub>	Collector-base breakdown voltage				
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	450		V
V <sub>EBO</sub>	Emitter-base breakdown voltages				
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =16A; I <sub>B</sub> =3.2A		1.5	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =24A; I <sub>B</sub> =5A		5	V
V <sub>CE(sat-3)</sub>	Collector-emitter saturation voltages				
h <sub>FE-1</sub>	Forward current transfer ratio				
h <sub>FE-2</sub>	Forward current transfer ratio				
V <sub>BE(set)1</sub>	Base-emitter saturation voltages	I <sub>C</sub> =16A; I <sub>B</sub> =3.2A		2.0	V
V <sub>BE(set)2</sub>	Base-emitter saturation voltages				
V <sub>BE(set)3</sub>	Base-emitter saturation voltages				
f <sub>T</sub>	Transition frequency at f=1MHz				

